

2 – 6 GHz Cascadable GaAs MMIC Amplifier

Technical Data

MGA-64135

Features

- **Cascadable 50 Ω Gain Block**
- **Broadband Performance:**
2–6 GHz
12.0 dB Typical Gain
 ± 0.8 dB Gain Flatness
12.0 dBm P₁ dB
- **Single Supply Bias**
- **Cost Effective Ceramic Microstrip Package**

Description

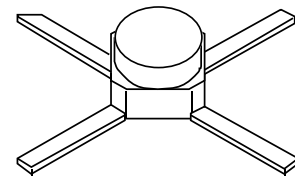
The MGA-64135 is a high performance gallium arsenide Monolithic Microwave Integrated Circuit (MMIC) housed in a cost effective, microstrip package. This device is designed for use as a general purpose 50 ohm gain block in the 2 to 6 GHz frequency range. Typical

applications include narrow and broadband IF and RF amplifiers for commercial, industrial, and military requirements.

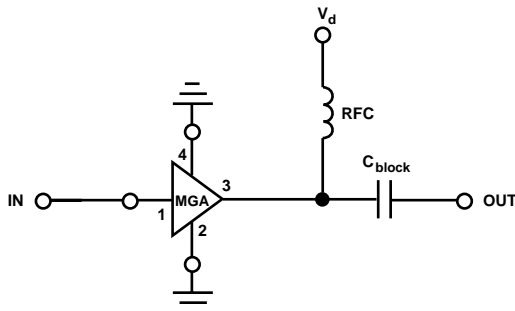
This MMIC is a cascade of two stages, each utilizing shunt feedback to establish a broadband impedance match. The source of each stage is AC grounded to allow biasing from a single positive power supply. The interstage blocking capacitor as well as a resistive “self-bias” network are included on chip.

The die is fabricated using HP’s nominal .5 micron recessed Schottky-barrier-gate, gold metallization and silicon nitride passivation to achieve excellent performance, uniformity, and reliability.

35 Micro-X Package



Typical Biasing Configuration



MGA-64135 Absolute Maximum Ratings

Symbol	Parameter	Units	Absolute Maximum ^[1]
V _d	Device Voltage	V	12
P _{diss}	Total Power Dissipation ^[2]	mW	650
P _{in}	CW RF Input Power	dBm	+13
T _{ch}	Channel Temperature	°C	175
T _{STG}	Storage Temperature ^[3]	°C	-65 to 175

Thermal Resistance:	$\theta_{jc} = 150^{\circ}\text{C}/\text{W}^{[4]}$; T _{CH} = 150°C
Liquid Crystal Measurement:	1 μm Spot Size ^[5]

Notes:

1. Operation of this device above any one of these parameters may cause permanent damage.
2. Derate linearly at 8.3 mW/°C for T_{CASE} > 103°C.
3. Storage above +150°C may tarnish the leads of this package making it difficult to solder into a circuit. After a device has been soldered into a circuit, it may be safely stored up to 175°C.
4. The thermal resistance value is based on measurements taken with the device soldered to a 25 mil Teflon PCB.
5. The small spot size of this technique results in a higher, though more accurate determination of θ_{jc} than do alternate methods. See MEASUREMENTS section for more information.

MGA-64135 Electrical Specifications, T_A = 25°C

Symbol	Parameters and Test Conditions: V _a = 10 V, Z _o = 50 Ω	Units	Min.	Typ.	Max.
G _P	Power Gain (S ₂₁ ²) f = 2 to 6 GHz	dB	10.0	12.0	
ΔG _P	Gain Flatness f = 2 to 6 GHz	dB		± 1.20	
—	Gain Variation vs. Temperature T _{CASE} = -25°C to +85°C f = 2 to 6 GHz	dB		± 0.5	
VSWR	Input VSWR f = 2 to 6 GHz			1.5:1	2.0:1
	Output VSWR f = 2 to 6 GHz			1.4:1	2.0:1
P _{1 dB}	Output Power at 1 dB Gain Compression f = 2 to 6 GHz	dBm	10.0	12.0	
NF	50 Ω Noise Figure f = 2 to 6 GHz	dB		7.5	
—	Reverse Isolation (S ₂₁ ²) f = 2 to 6 GHz	dB		35	
I _d	Device Current	mA	35	50	65

MGA-64135 Typical Performance, $T_A = 25^\circ\text{C}$

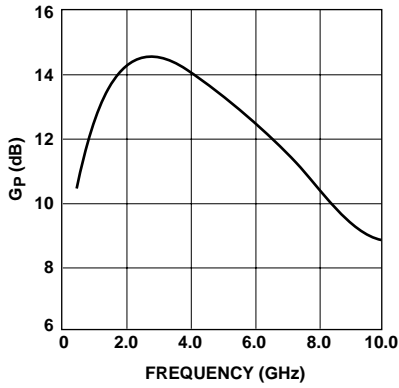


Figure 1. Power Gain vs. Frequency, $V_d = 10\text{ V}$.

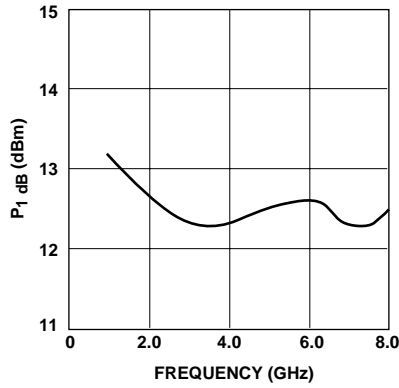


Figure 2. Output Power @ 1 dB Gain Compression vs. Frequency, $V_d = 10\text{ V}$.

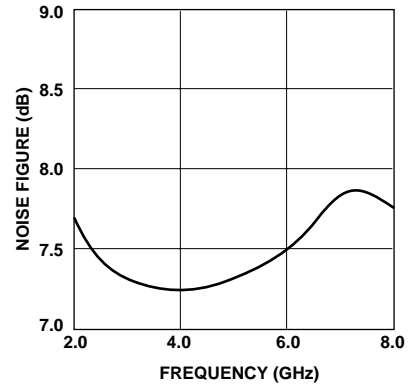


Figure 3. Noise Figure vs. Frequency, $V_d = 10\text{ V}$.

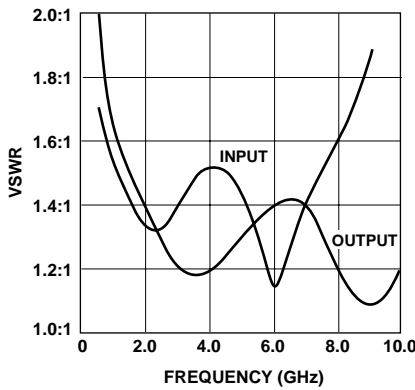


Figure 4. VSWR vs. Frequency, $V_d = 10\text{ V}$.

MGA-64135 Typical Scattering Parameters ($Z_0 = 50\ \Omega$, $T_A = 25^\circ\text{C}$, $V_d = 10\text{ V}$)

Freq. GHz	S_{11}		S_{21}			S_{12}			S_{22}	
	Mag	Ang	dB	Mag	Ang	dB	Mag	Ang	Mag	Ang
0.5	.27	-38	10.6	3.38	174	-31.0	.028	-13	.38	-41
1.0	.18	-44	12.9	4.42	-9	-33.1	.022	-20	.26	-48
2.0	.14	-67	14.3	5.21	-54	-34.9	.018	-19	.16	-59
3.0	.17	-91	14.5	5.33	-93	-37.1	.014	-21	.11	-75
4.0	.20	-105	14.2	5.11	-131	-37.8	.013	-15	.11	-71
5.0	.18	-114	13.6	4.79	-167	-37.3	.014	-10	.14	-57
6.0	.07	-162	12.8	4.35	157	-38.5	.012	-1	.17	-41
7.0	.15	96	11.8	3.89	123	-36.0	.016	3	.16	-42
8.0	.23	76	10.8	3.46	92	-34.3	.019	4	.10	-54
9.0	.32	63	9.5	2.98	63	-29.3	.034	12	.04	159
10.0	.43	52	8.6	2.68	38	-27.6	.041	-11	.09	116

35 Micro-X Package Dimensions

